

# Dual N-channel MOSFET (common drain)

ELM18814BA-S

## General description

ELM18814BA-S uses advanced trench technology to provide excellent  $R_{ds(on)}$ , low gate charge and operation with gate voltages as low as 1.8V and internal ESD protection.

## Features

- $V_{ds}=20V$
- $I_d=7.5A$  ( $V_{gs}=10V$ )
- $R_{ds(on)} < 16m\Omega$  ( $V_{gs}=10V$ )
- $R_{ds(on)} < 18m\Omega$  ( $V_{gs}=4.5V$ )
- $R_{ds(on)} < 24m\Omega$  ( $V_{gs}=2.5V$ )
- $R_{ds(on)} < 34m\Omega$  ( $V_{gs}=1.8V$ )
- ESD Rating : 2500V HBM

## Maximum absolute ratings

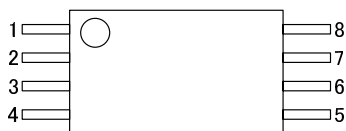
Parameter	Symbol	Limit	Unit	Note
Drain-source voltage	$V_{ds}$	20	V	
Gate-source voltage	$V_{gs}$	$\pm 12$	V	
Continuous drain current	$I_d$	7.5	A	1
		6.0		
Pulsed drain current	$I_{dm}$	30	A	2
Power dissipation	$P_d$	1.50	W	1
		0.96		
Junction and storage temperature range	$T_j, T_{stg}$	-55 to 150	$^{\circ}C$	

## Thermal characteristics

Parameter		Symbol	Typ.	Max.	Unit	Note
Maximum junction-to-ambient	$t \leq 10s$	$R\theta_{ja}$	64	83	$^{\circ}C/W$	1
Maximum junction-to-ambient	Steady-state		89	120	$^{\circ}C/W$	
Maximum junction-to-lead	Steady-state	$R\theta_{jl}$	53	70	$^{\circ}C/W$	3

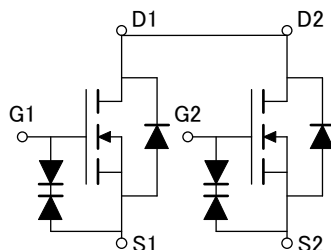
## Pin configuration

TSSOP-8 (TOP VIEW)



Pin No.	Pin name
1	DRAIN1/DRAIN2
2	SOURCE1
3	SOURCE1
4	GATE1
5	GATE2
6	SOURCE2
7	SOURCE2
8	DRAIN1/DRAIN2

## Circuit



# Dual N-channel MOSFET (common drain)

## ELM18814BA-S

### Electrical characteristics

T<sub>a</sub>=25°C

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
<b>STATIC PARAMETERS</b>						
Drain-source breakdown voltage	BV <sub>dss</sub>	I <sub>d</sub> =250 μA, V <sub>gs</sub> =0V	20			V
Zero gate voltage drain current	I <sub>dss</sub>	V <sub>ds</sub> =16V			1	μA
		V <sub>gs</sub> =0V		T <sub>j</sub> =55°C	5	
Gate-body leakage current	I <sub>gss</sub>	V <sub>ds</sub> =0V, V <sub>gs</sub> =±10V			10	μA
Gate-source breakdown voltage	BV <sub>gso</sub>	V <sub>ds</sub> =0V, I <sub>g</sub> =±250 μA	±12			V
Gate threshold voltage	V <sub>gs(th)</sub>	V <sub>ds</sub> =V <sub>gs</sub> , I <sub>d</sub> =250 μA	0.50	0.71	1.00	V
On state drain current	I <sub>d(on)</sub>	V <sub>gs</sub> =4.5V, V <sub>ds</sub> =5V	30			A
Static drain-source on-resistance	R <sub>ds(on)</sub>	V <sub>gs</sub> =10V		13	16	mΩ
		I <sub>d</sub> =7.5A		18	22	
		V <sub>gs</sub> =4.5V, I <sub>d</sub> =7A		15	18	mΩ
		V <sub>gs</sub> =2.5V, I <sub>d</sub> =6A		19	24	mΩ
		V <sub>gs</sub> =1.8V, I <sub>d</sub> =5A		26	34	mΩ
Forward transconductance	G <sub>fs</sub>	V <sub>ds</sub> =5V, I <sub>d</sub> =7.5A		30		S
Diode forward voltage	V <sub>sd</sub>	I <sub>s</sub> =1A, V <sub>gs</sub> =0V		0.74	1.00	V
Max. body-diode continuous current	I <sub>s</sub>				2.5	A
<b>DYNAMIC PARAMETERS</b>						
Input capacitance	C <sub>iss</sub>	V <sub>gs</sub> =0V, V <sub>ds</sub> =10V, f=1MHz		1390		pF
Output capacitance	C <sub>oss</sub>			190		pF
Reverse transfer capacitance	C <sub>rss</sub>			150		pF
Gate resistance	R <sub>g</sub>	V <sub>gs</sub> =0V, V <sub>ds</sub> =0V, f=1MHz		1.5		Ω
<b>SWITCHING PARAMETERS</b>						
Total gate charge	Q <sub>g</sub>	V <sub>gs</sub> =4.5V, V <sub>ds</sub> =10V, I <sub>d</sub> =7.5A		15.4		nC
Gate-source charge	Q <sub>gs</sub>			1.4		nC
Gate-drain charge	Q <sub>gd</sub>			4.0		nC
Turn-on delay time	t <sub>d(on)</sub>	V <sub>gs</sub> =5V, V <sub>ds</sub> =10V R <sub>l</sub> =1.3 Ω, R <sub>gen</sub> =3 Ω		6.2		ns
Turn-on rise time	t <sub>r</sub>			11.0		ns
Turn-off delay time	t <sub>d(off)</sub>			40.5		ns
Turn-off fall time	t <sub>f</sub>			10.0		ns
Body diode reverse recovery time	t <sub>rr</sub>	I <sub>f</sub> =7.5A, dI/dt=100A/μs		15.0		ns
Body diode reverse recovery charge	Q <sub>rr</sub>	I <sub>f</sub> =7.5A, dI/dt=100A/μs		5.1		nC

#### NOTE :

1. The value of R<sub>θja</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board of 2oz. Copper, in still air environment with T<sub>a</sub>=25°C. The value in any given applications depends on the user's specific board design, The current rating is based on the t ≤ 10s thermal resistance rating.
2. Repetitive rating, pulse width limited by junction temperature.
3. The R<sub>θja</sub> is the sum of the thermal impedance from junction to lead R<sub>θjl</sub> and lead to ambient.
4. The static characteristics in Figures 1 to 6 are obtained using 80μs pulses, duty cycle 0.5%max.
5. These tests are performed with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>a</sub>=25°C. The SOA curve provides a single pulse rating.

# Dual N-channel MOSFET (common drain)

ELM18814BA-S

## Typical electrical and thermal characteristics

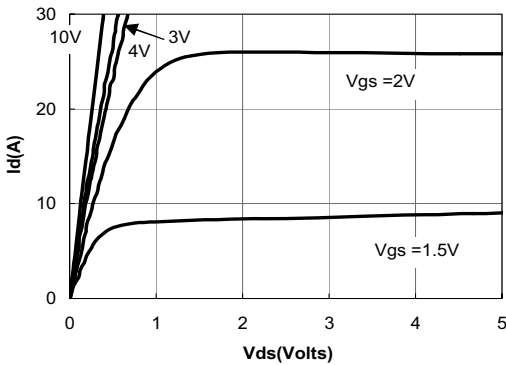


Figure 1: On-Regions Characteristics

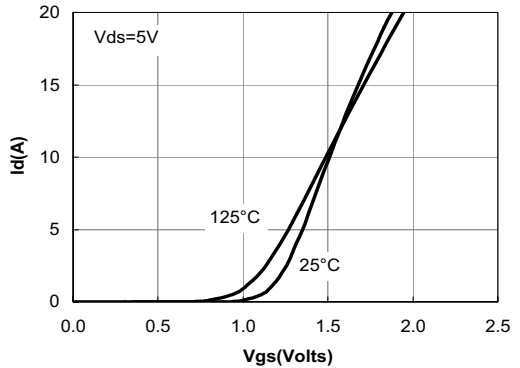


Figure 2: Transfer Characteristics

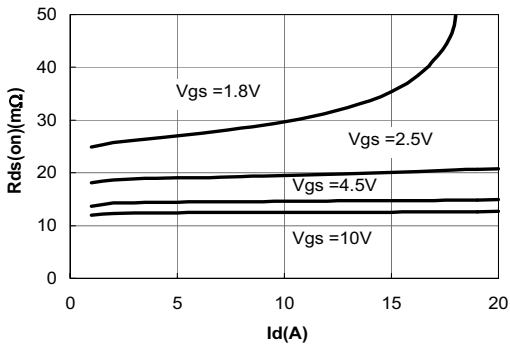


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

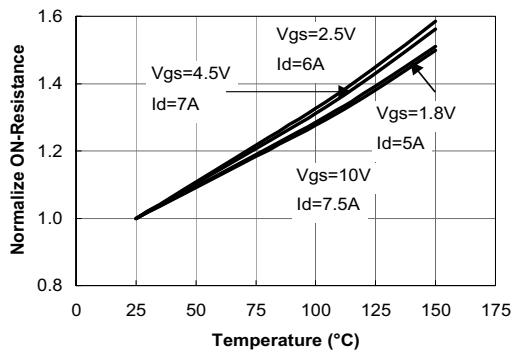


Figure 4: On-Resistance vs. Junction Temperature

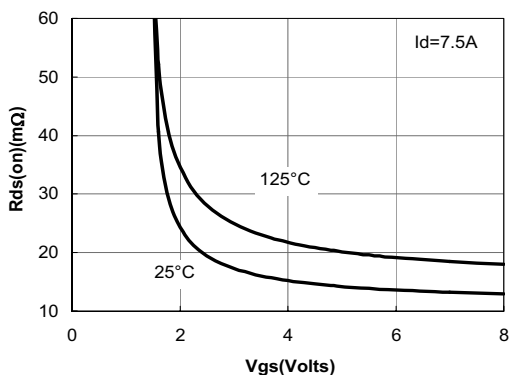


Figure 5: On-Resistance vs. Gate-Source Voltage

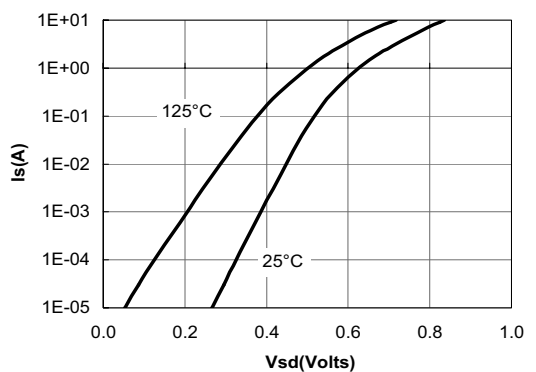


Figure 6: Body-Diode Characteristics

# Dual N-channel MOSFET (common drain)

## ELM18814BA-S

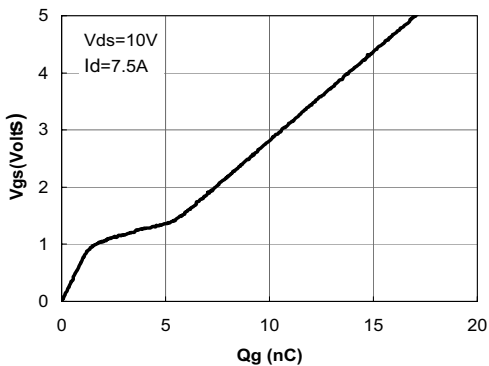


Figure 7: Gate-Charge Characteristics

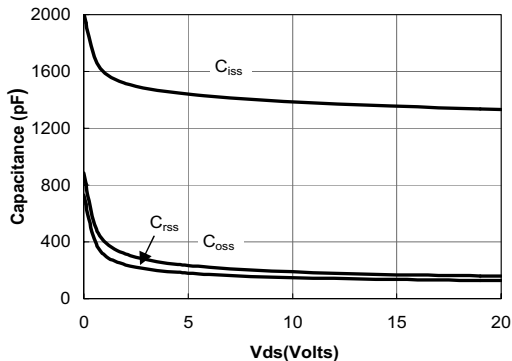


Figure 8: Capacitance Characteristics

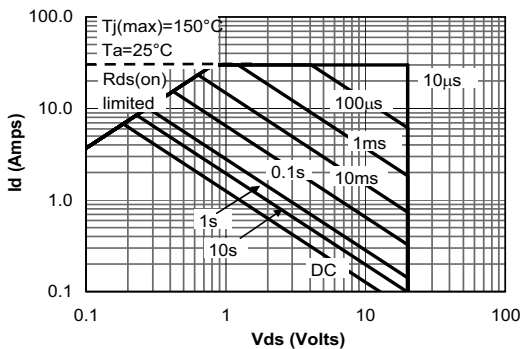


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

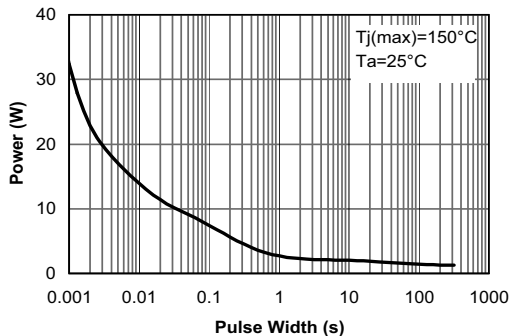


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

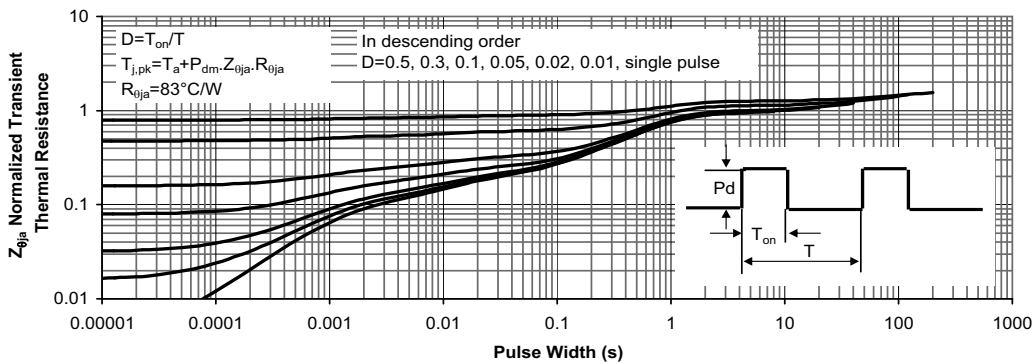


Figure 11: Normalized Maximum Transient Thermal Impedance